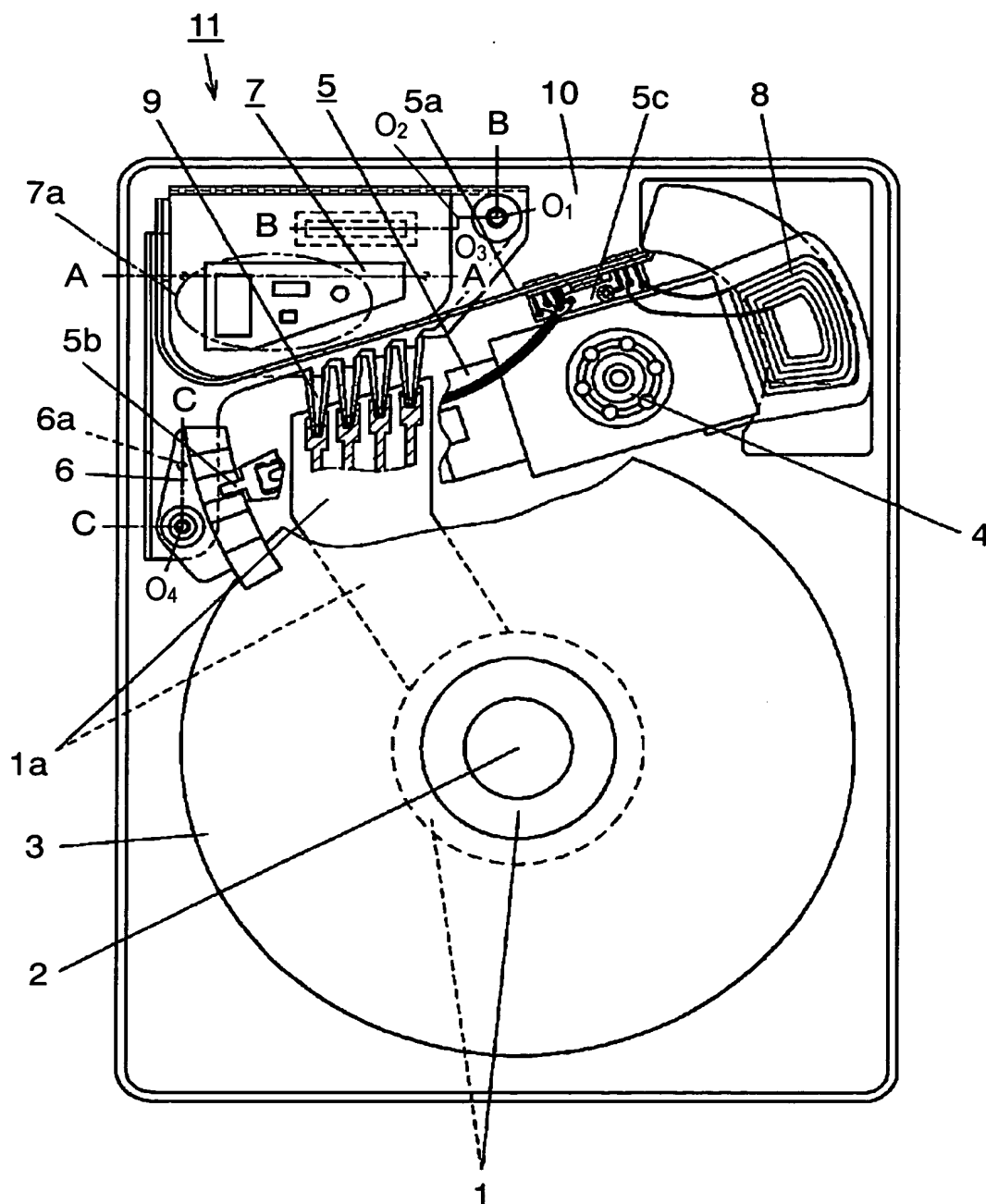


1/13

FIG. 1





3/13

FIG. 3A

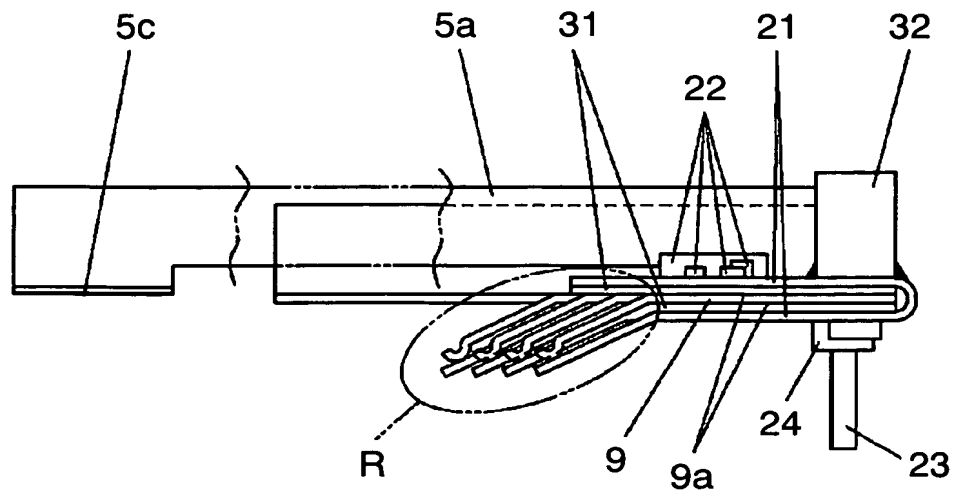


FIG. 3B

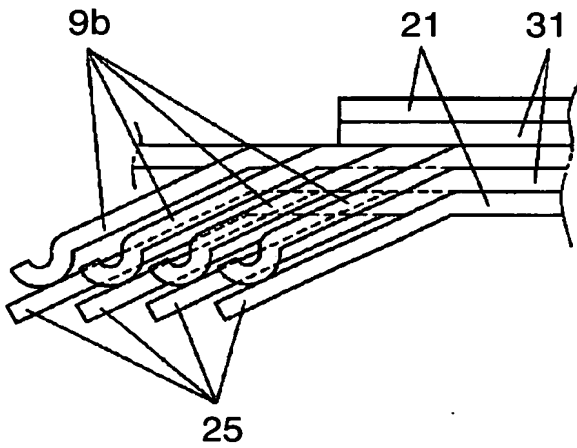
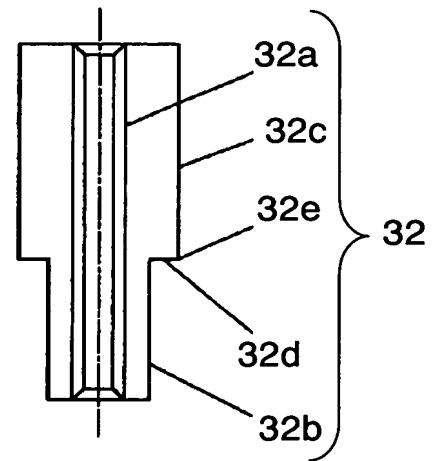


FIG. 3C



4/13

FIG. 4A

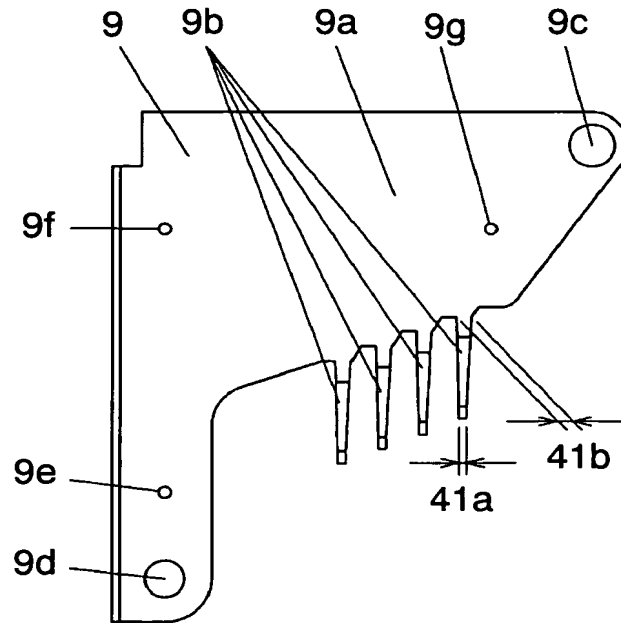
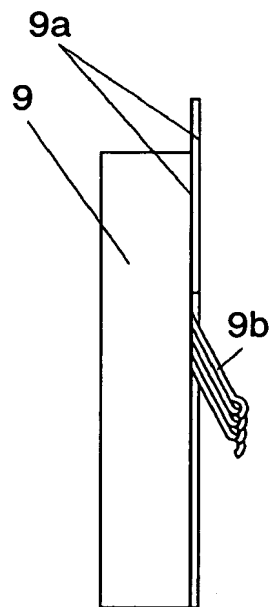


FIG. 4B



5/13

FIG. 5A

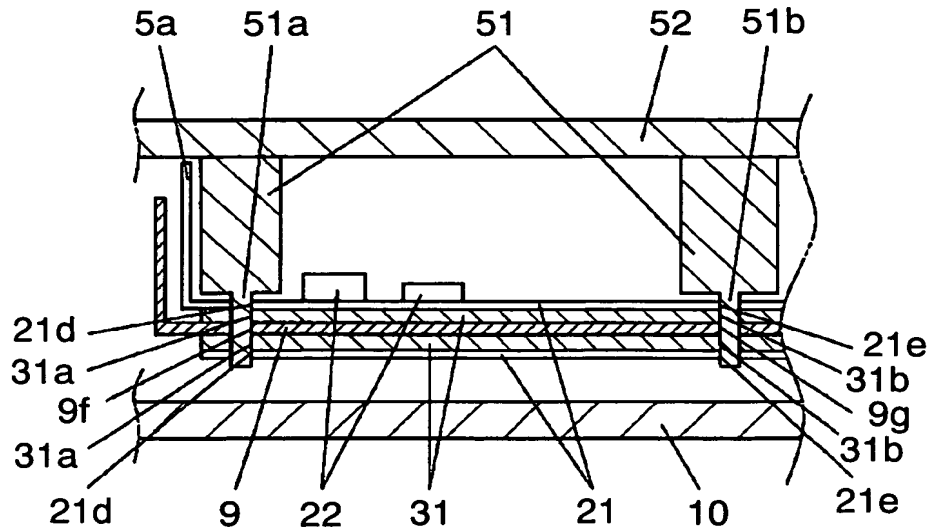


FIG. 5B

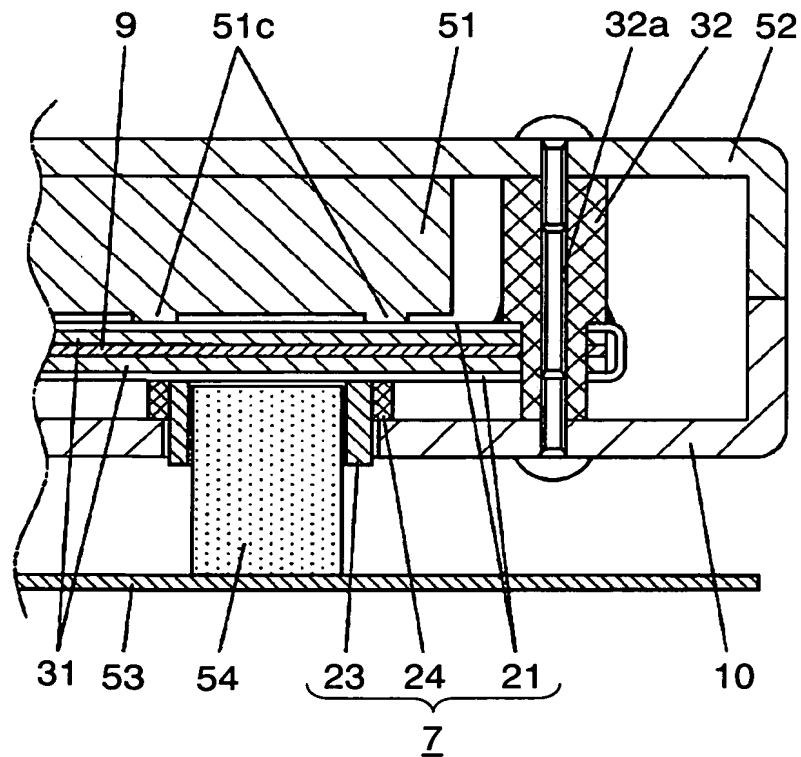
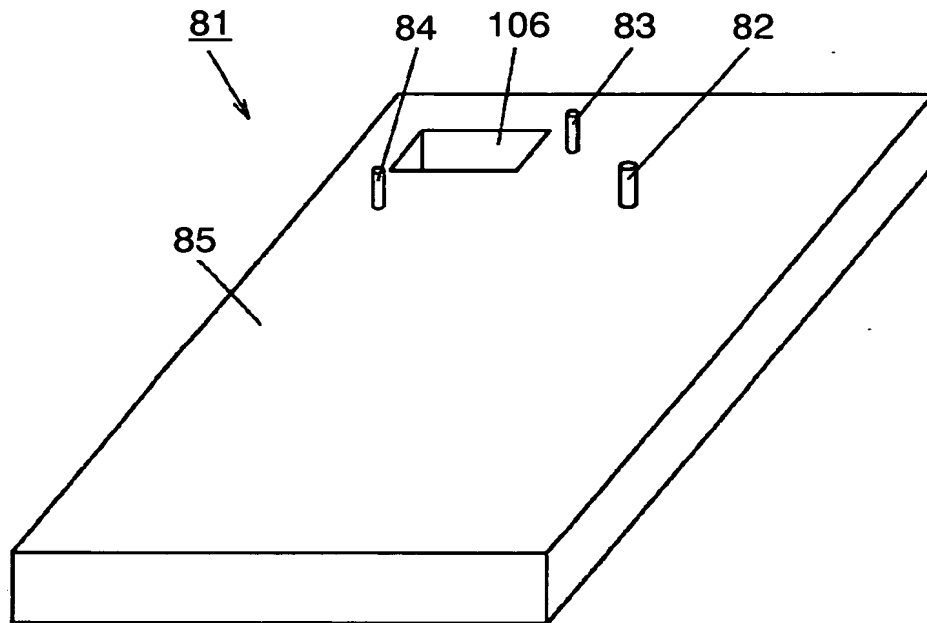


Fig. 1 is a cross-sectional view of a semiconductor device. It shows a substrate 1a with a base layer 1b. On top of 1b are several vertical structures 9, each with a top layer 9b. A layer 21 is on top of the structures 9. A layer 25 is on top of the layer 21. Dimensions W1, W2, and W3 are indicated at the bottom, corresponding to the widths of the structures 9, the base layer 1b, and the layer 21, respectively.

7/13

FIG. 8



8/13

FIG. 9A

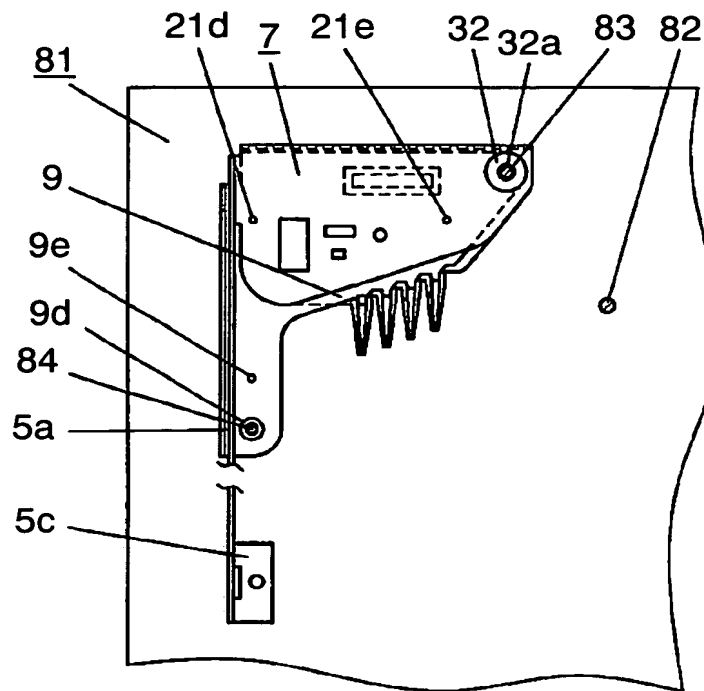
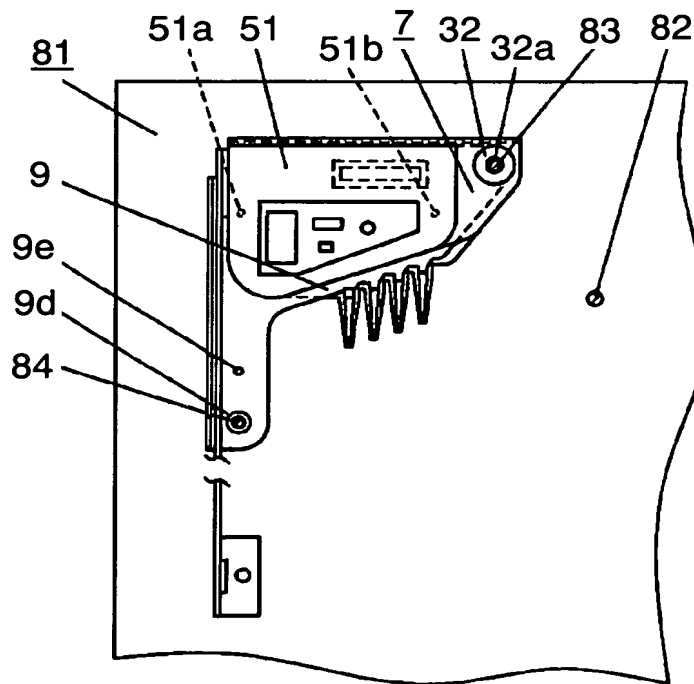


FIG. 9B





9/13

**FIG. 10A**

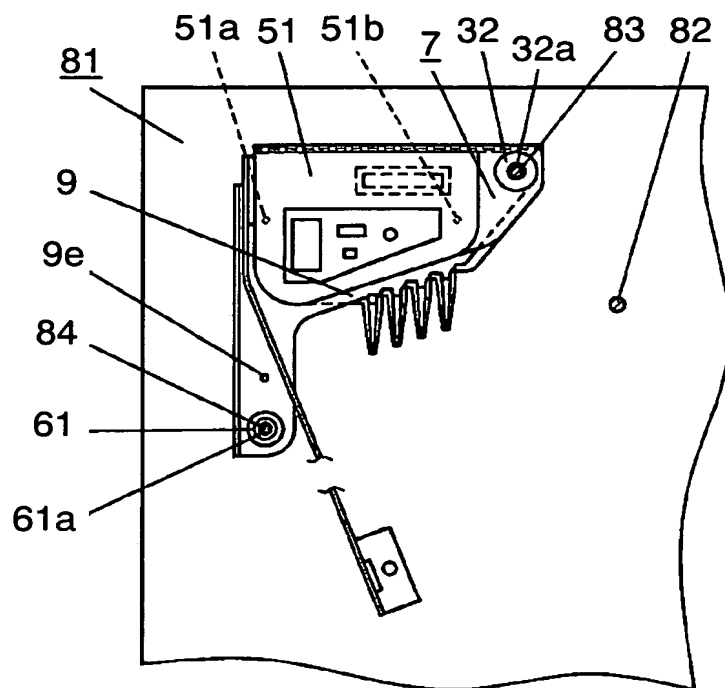
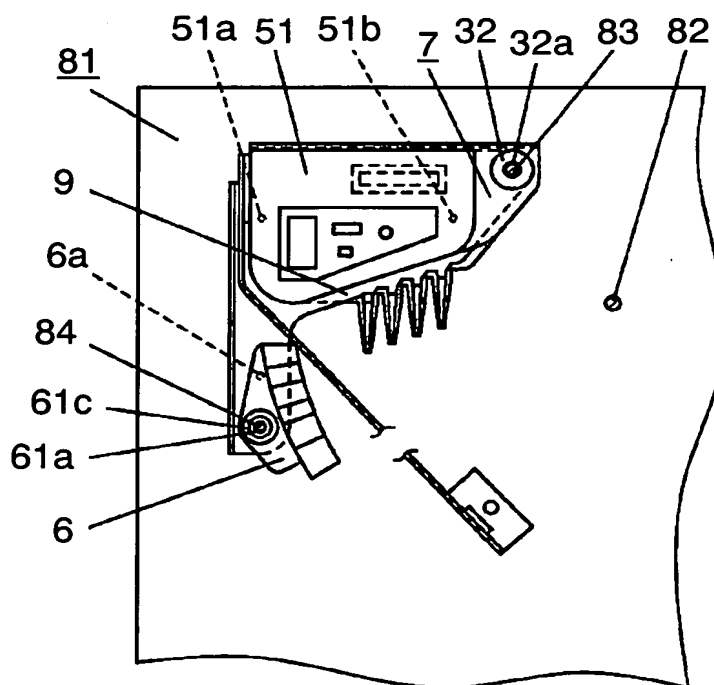


FIG. 10B





11/13

FIG. 12

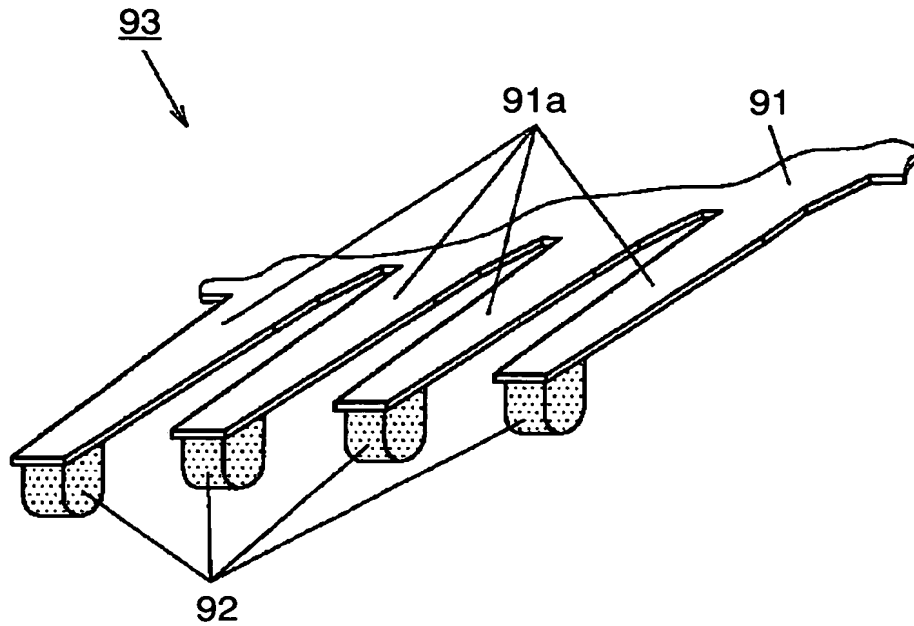
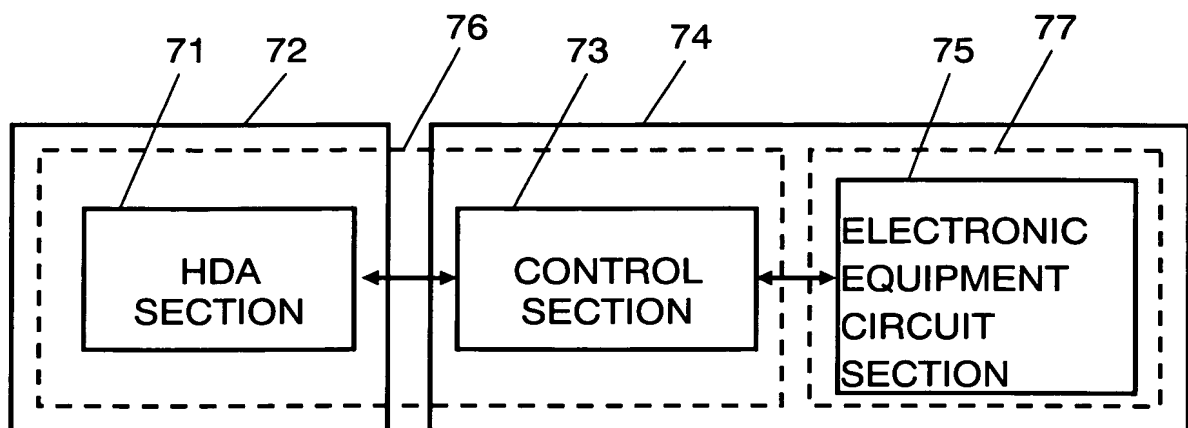
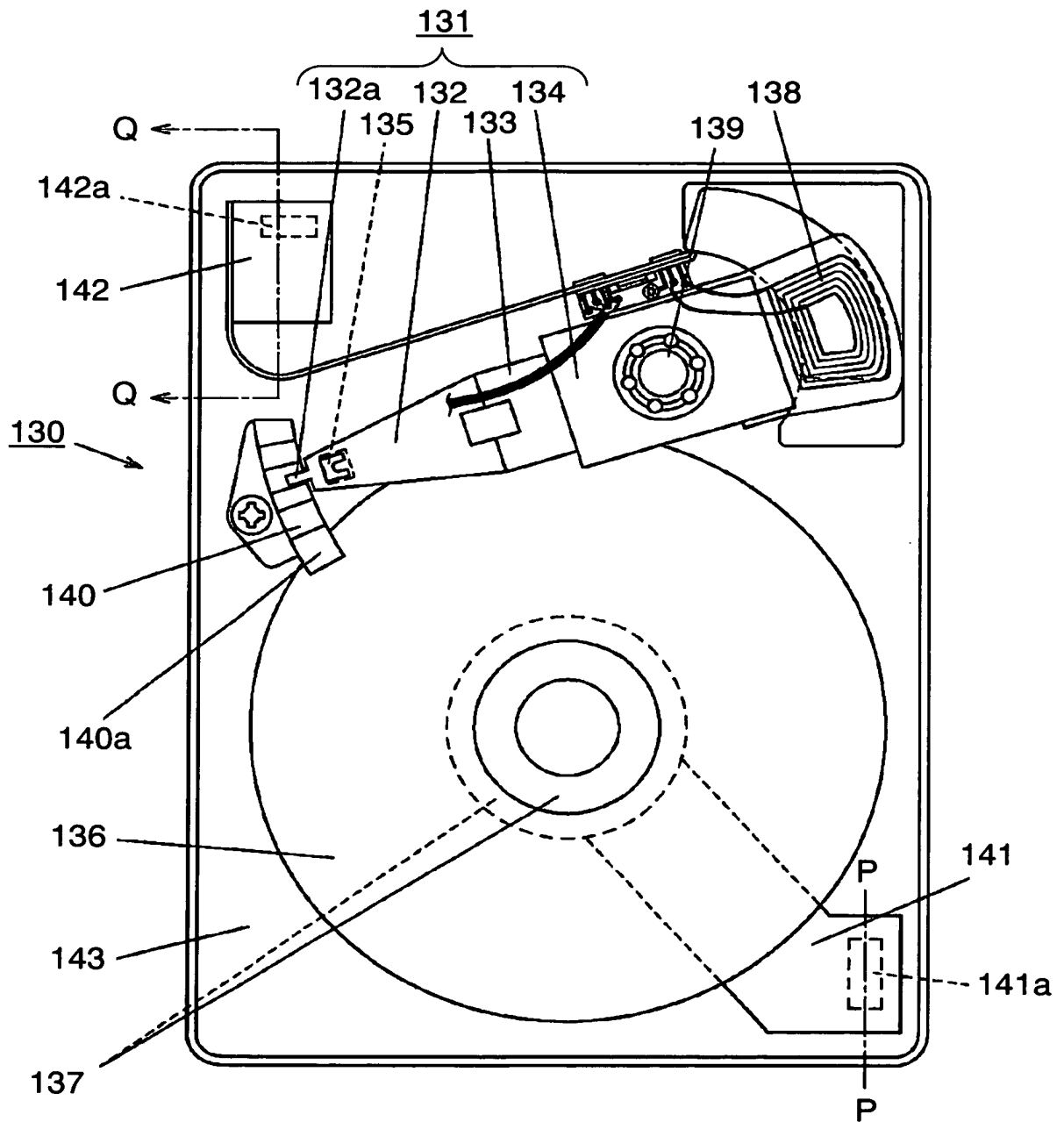


FIG. 13



12/13

FIG. 14



13/13

FIG. 15A

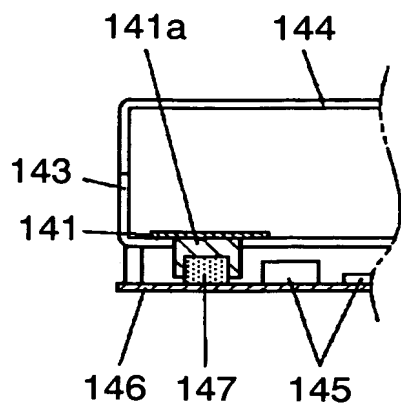


FIG. 15B

